

In response to the Advisory Action of February, 2003, please amend the above-identified application as follows:

**In the Claims:**

Please amend claims 11 - 17 as follows:

*Sub D11*

11. (THRICE AMENDED) A method for removing cohesive coatings *112/2 ?*  
from a plurality of substrates having dense submicron topography containing  
prominent sidewalls, comprising the steps of:

5      placing a quartz gas distribution plate, connected to a pressure *matter of choice* - *new*  
regulated gas supply, in an open tank containing a liquid chemical;  
submerging and placing a substrate carrier, containing a plurality of  
substrates, on said quartz gas distribution plate so that said substrates  
are aligned *align* and in a vertical position relative to said quartz gas  
distribution plate;

10      intermittently changing a pressure of said regulated gas supply for  
generating a turbulent vertical agitation, said distribution plate directs gas  
bubbles between and parallel to each surface of said substrates aligned  
thereabove, said turbulent vertical agitation providing a chemical-  
mechanical scrubbing;

15      removing said substrate carrier from said chemical liquid.

*C1*

12. (THRICE AMENDED) The method according to claim 11 wherein  
said quartz gas distribution plate having distribution means for generating an  
array of gas bubbles, each row of said array corresponding to a substrate position

20 of said substrate carrier.

13. (THRICE AMENDED) The method according to claim 11 wherein said pressure regulated gas supply is nitrogen gas.

25 14. (THRICE AMENDED) The method according to claim 11 wherein using a quartz gas distribution plate is compatible with aggressive chemicals for removing cohesive residues in metal sidewalls that are coated with polymer.

30 15. (THRICE AMENDED) A method for stripping cohesive photoresist from a plurality of semiconductor wafers having dense submicron topography containing prominent sidewalls, comprising the steps of:  
horizontally placing a quartz gas distribution plate, connected to a pressure regulated gas supply, in an open tank containing a photoresist stripping chemical;  
35 submerging and placing a wafer cassette containing a plurality of wafers on said quartz gas distribution plate so that said wafers are aligned and in a vertical position relative to said quartz gas distribution plate;  
intermittently changing said pressure of said pressure regulated gas supply for generating a turbulent vertical agitation, said distribution plate directs  
40 gas bubbles between and parallel to each surface of said wafers aligned thereabove, said turbulent vertical agitation providing a chemical-mechanical scrubbing;

Sub D2  
45 removing said wafer cassette from said photoresist stripping liquid.

C1  
16. (THRICE AMENDED) The method according to claim 11 wherein said quartz gas distribution plate having distribution means for generating an array of gas bubbles, each row of said array corresponding to a wafer position of said wafer cassette.

50 17. (THRICE AMENDED) The method according to claim 11 wherein said pressure regulated gas supply is nitrogen gas.

Sub D3  
C2  
55 18. (THRICE AMENDED) The method according to claim 11 wherein using a quartz gas distribution plate is compatible with aggressive chemicals for removing cohesive residues in metal sidewalls that are coated with cohesive photoresist.

#### REMARKS/ARGUMENTS

Claims 11 - 18 have been amended. No new matter has been added.

Claims 11 - 18 have been rewritten to further clarify the process while removing any claimed reference to the apparatus in response to the Examiner's kind suggestions.